TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS056

CD4071B, CD4072B, CD4075B Types

CMOS OR Gates

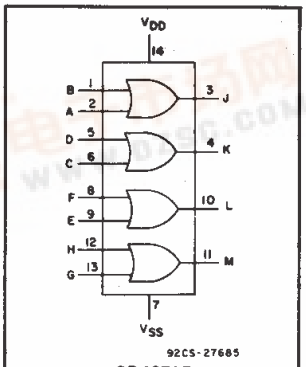
High-Voltage Types (20-Volt Rating)

CD4071B Quad 2-Input OR Gate
CD4072B Dual 4-Input OR Gate
CD4075B Triple 3-Input OR Gate

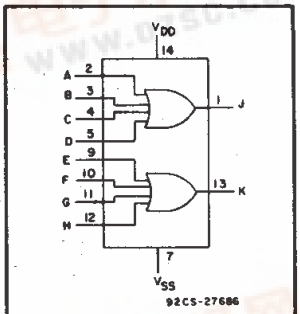
■ CD4071B, CD4072B, and CD4075B OR gates provide the system designer with direct implementation of the positive-logic OR function and supplement the existing family of CMOS gates. The CD4071, CD4072, and CD4075 types are supplied in 14-lead dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

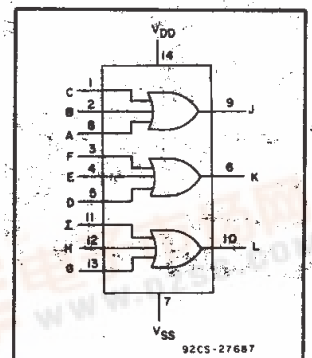
- Medium-Speed Operation-t_{PLH}, t_{PHL} = 60 ns (typ.) at V_{DD} = 10 V
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Standardized, symmetrical output characteristics
- Noise margin (over full package temperature range)
  1 V at V_{DD} = 5 V
  2 V at V_{DD} = 10 V
  2.5 V at V_{DD} = 15 V
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"



CD4071B
FUNCTIONAL DIAGRAM



CD4072B
FUNCTIONAL DIAGRAM



CD4075B
FUNCTIONAL DIAGRAM

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package-Temperature Range)	3	18	V

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
								+25			
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	0.25	0.25	7.5	7.5	–	0.01	0.25	μA
	–	0,10	10	0.5	0.5	15	15	–	0.01	0.5	
	–	0,15	15	1	1	30	30	–	0.01	1	
	–	0,20	20	5	5	150	150	–	0.02	5	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3 4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	0.5, 4.5	–	5	1.5				—	—	1.5	V
	1, 9	–	10	3				—	—	3	
	1.5,13.5	–	15	4				—	—	4	
Input High Voltage, V_{IH} Min.	4.5	–	5	3.5				3.5	—	—	
	9	–	10	7				7	—	—	
	13.5	–	15	11				11	—	—	
Input Current I_{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) ..... -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

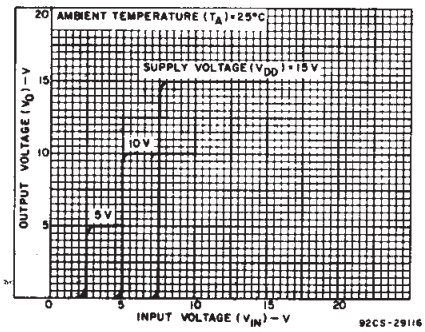


Fig. 1 — Typical voltage transfer characteristics.

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C, Input t_r, t_f = 20 ns, and C_L = 50 pF, R_L = 200 kΩ

CHARACTERISTIC	TEST CONDITIONS		ALL TYPES LIMITS		UNITS
		V_{DD} VOLTS	TYP.	MAX.	
Propagation Delay Time, t_{PHL}, t_{PLH}		5	125	250	ns
		10	60	120	
		15	45	90	
Transition Time, t_{THL}, t_{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C_{IN}	Any Input	—	5	7.5	pF

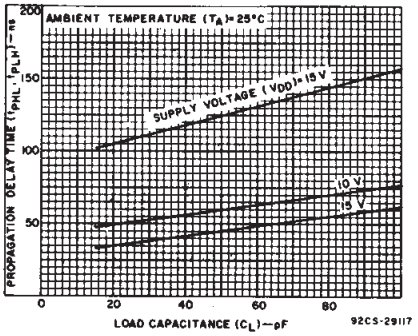


Fig. 2 — Typical propagation delay time as a function of load capacitance.

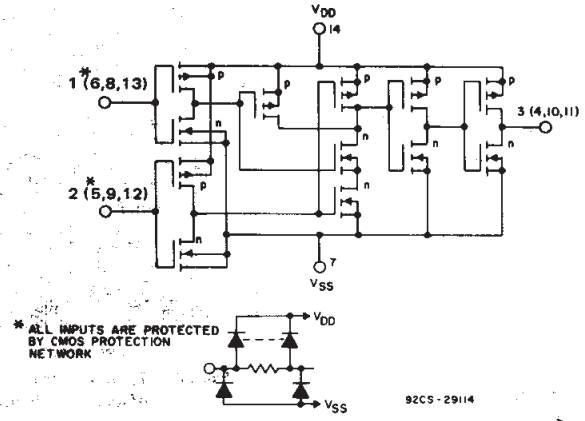


Fig. 3 — Schematic diagram for CD4071B (1 of 4 identical gates).

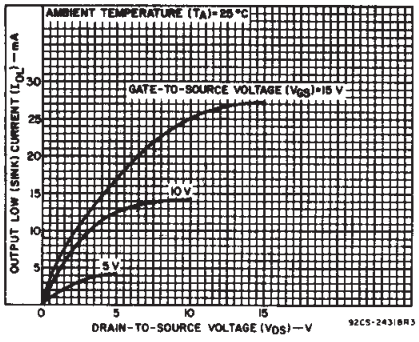


Fig. 4 — Typical output low (sink) current characteristics.

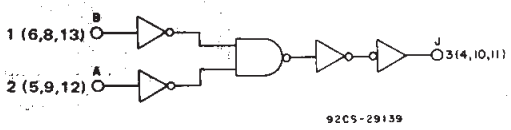


Fig. 5 — Logic diagram for CD4071B (1 of 4 identical gates).

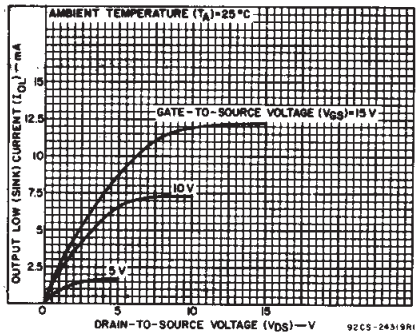


Fig. 6 — Minimum output low (sink) current characteristics.

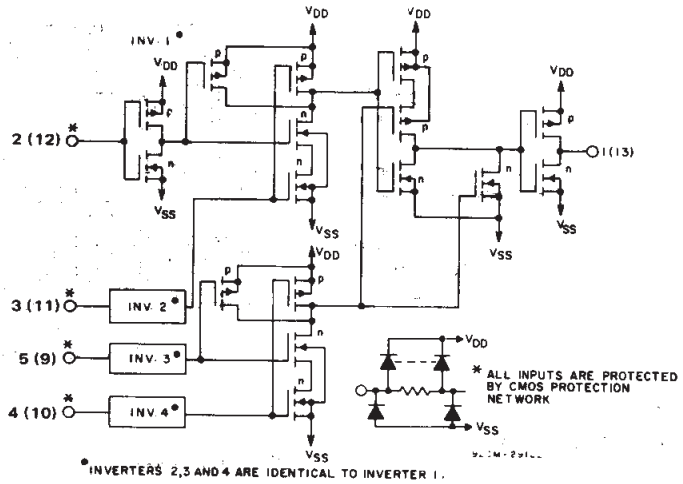


Fig. 7 – Schematic diagram for CD4072B (1 of 2 identical gates).

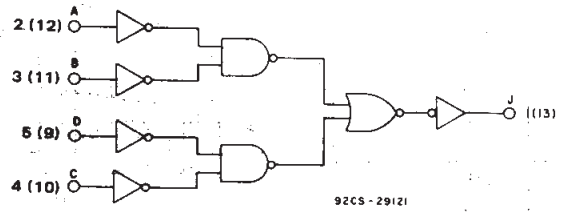


Fig. 9 – Logic diagram for CD4072B (1 of 2 identical gates).

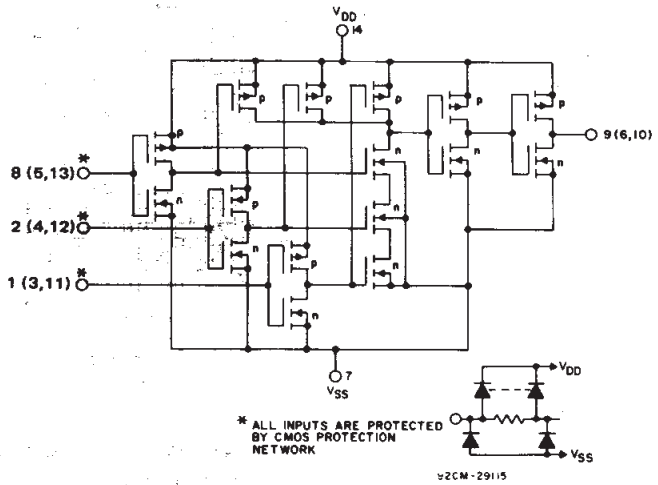


Fig. 11 – Schematic diagram for CD4075B (1 of 3 identical gates).

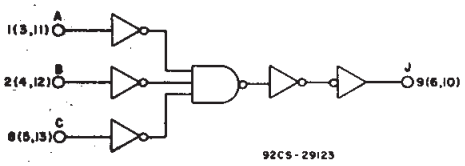


Fig. 13 – Logic diagram for CD4075B (1 of 3 identical gates).

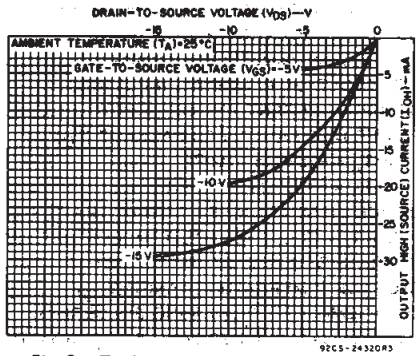


Fig. 8 – Typical output high (source) current characteristics.

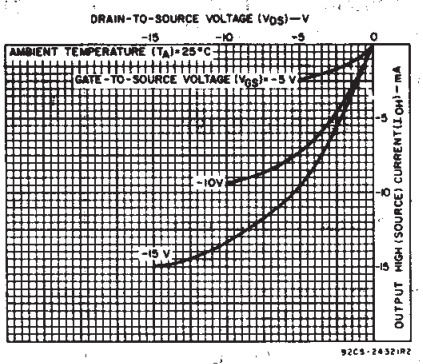


Fig. 10 – Minimum output high (source) current characteristics.

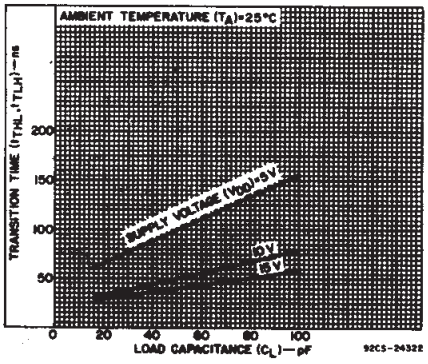


Fig. 12 – Typical transition time as a function of load capacitance.

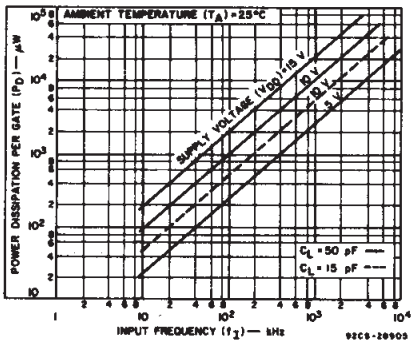
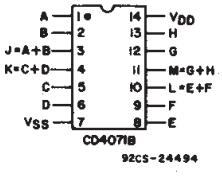
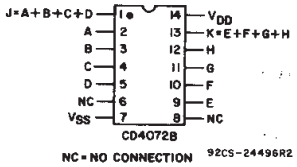
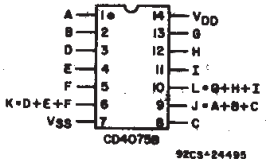


Fig. 14 – Typical dyanamic power dissipation as a function of frequency.

TERMINAL ASSIGNMENTS (TOP VIEW)







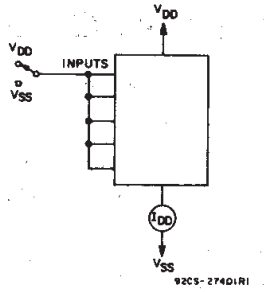


Fig. 15 — Quiescent device current test circuit.

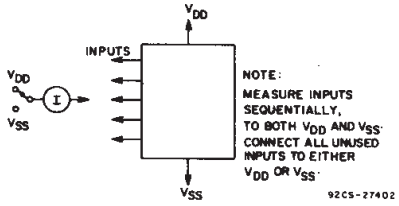


Fig. 16 — Input current test circuit.

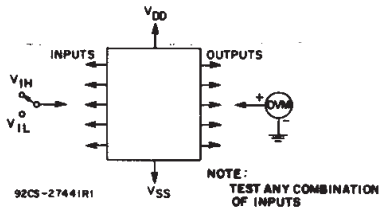
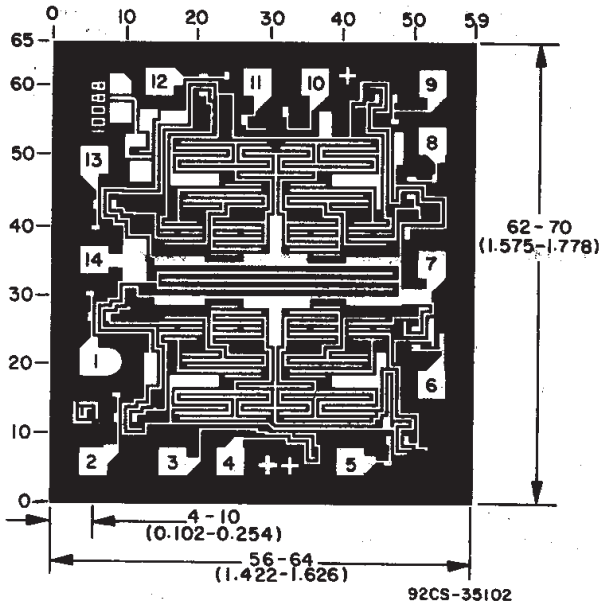
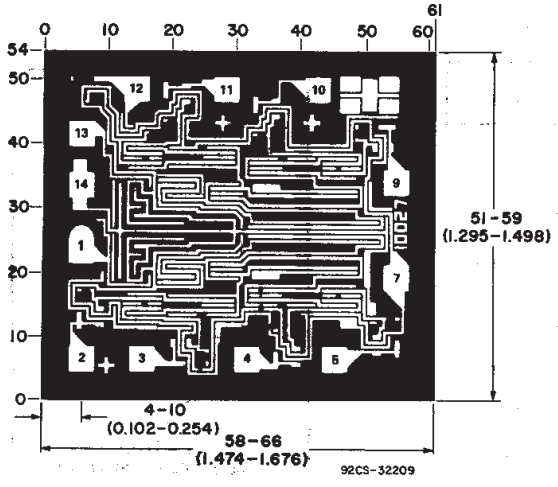


Fig. 17 — Input-voltage test circuit.

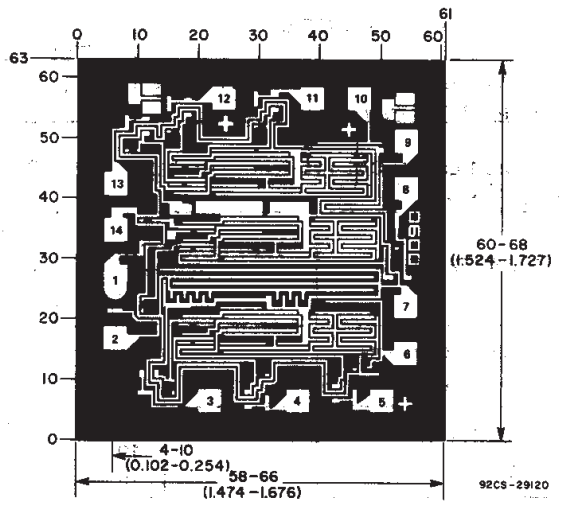
Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).



Chip dimensions and pad layout for CD4071B.



Chip dimensions and pad layout for CD4072B.



Chip dimensions and pad layout for CD4075B.

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